L Number	Hits	Search Text	DB	Time stamp
-	83	heat near sink with ((bottom adj surface) near5 expos$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:45
-	6	(heat near sink with ((bottom adj surface) near5 expos$3)) and conductive near plate and semiconductor near (chip device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:46
-	2808	(257/625,675,706,707,796).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:50
-	2264	(438/122,123,125).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:51
-	5	((257/625,675,706,707,796).CCLS.) and first near3 electrode and second near3 electrode with (smaller bigger)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:54
-	5	(((257/625,675,706,707,796).CCLS.) and first near3 electrode and second near3 electrode with (smaller bigger)) not (((438/122,123,125).CCLS.) and first near3 electrode and second near3 electrode with (smaller bigger))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:53
-	5	((438/122,123,125).CCLS.) and first near3 electrode and second near3 electrode with (smaller bigger)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:54
-	80	(((semiconductor and heat adj sink) and first near chip) and second near chip) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 06:57

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